Dual SPST Analog Switch, Low Voltage, Single Supply

The NLAS323 is a dual SPST (Single Pole, Single Throw) switch, similar to 1/2 a standard 4066. The device permits the independent selection of 2 analog/digital signals. Available in the US8 package.

The use of advanced 0.6 micron CMOS process, improves the R_{ON} resistance considerably compared to older higher voltage technologies.

Features

- On Resistance is 20 Ω Typical at 5.0 V
- Matching is $< 1.0 \Omega$ Between Sections
- 2.0 to 6.0 V Operating Range
- Ultra Low < 5.0 pC Charge Injection
- Ultra Low Leakage < 1.0 nA at 5.0 V, 25 C
- Wide Bandwidth > 200 MHz, -3.0 dB
- 2000 V ESD (Human Body Model)
- Ron Flatness $\pm 6.0 \Omega$ at 5.0 V
- US8 Package
- Independent, Positive Enable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

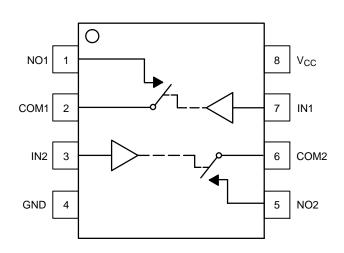


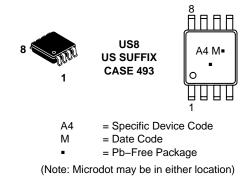
Figure 1. Pinout



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MARKING DIAGRAM



PIN ASSIGNMENT

1	NO1				
2	COM1				
3	IN2				
4	GND				
5	NO2				
6	COM2				
7	IN1				
8	V _{CC}				

FUNCTION TABLE

On/Off Enable Input	State of Analog Switch
L	Off
н	On

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

MAXIMUM RATINGS

Symbol		Parameter	Value	Unit
V _{CC}	DC Supply Voltage	-0.5 to +7.0	V	
VI	DC Input Voltage		-0.5 to +7.0	V
V _O	DC Output Voltage		-0.5 to +7.0	V
I _{IK}	DC Input Diode Current	V _I < GND	- 50	mA
I _{OK}	DC Output Diode Current	V _O < GND	- 50	mA
lo	DC Output Sink Current		±50	mA
I _{CC}	DC Supply Current per Supply F	Pin	±100	mA
I _{GND}	DC Ground Current per Ground	Pin	±100	mA
T _{STG}	Storage Temperature Range	-65 to +150	°C	
TL	Lead Temperature, 1 mm from C	Case for 10 Seconds	260	°C
TJ	Junction Temperature under Bia	IS	+ 150	°C
θ_{JA}	Thermal Resistance	(Note 1)	250	°C/W
P _D	Power Dissipation in Still Air at 8	35°C	250	mW
MSL	Moisture Sensitivity		Level 1	
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V–0 @ 0.125 in	
V _{ESD}	ESD Withstand Voltage	Human Body Model (Note 2) Machine Model (Note 3) Charged Device Model (Note 4)	> 2000 > 150 N/A	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected. 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2-ounce copper trace with no air flow.

2. Tested to EIA/JESD22-A114-A.

Tested to EIA/JESD22-A115-A. 3.

4. Tested to JESD22-C101-A.

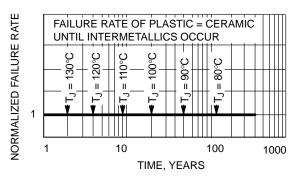
RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics			Max	Unit
V _{CC}	Positive DC Supply Voltage		2.0	5.5	V
V _{IN}	Digital Input Voltage (Enable)			5.5	V
V _{IO}	Static or Dynamic Voltage Across an Off Switch			V _{CC}	V
V _{IS}	Analog Input Voltage (NO, COM)			V _{CC}	V
T _A	Operating Temperature Range, All Package Types			+125	°C
t _r , t _f	Input Rise or Fall Time, (Enable Input)	$V_{cc} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{cc} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0





DC CHARACTERISTICS – Digital Section (Voltages Referenced to GND)

				Guaranteed Max Limit			
Symbol	Parameter	Condition	V _{cc}	–55 to 25°C	<85°C	<125°C	Unit
V _{IH}	Minimum High–Level Input Voltage, Enable Inputs		2.0 3.0 4.5 5.5	1.5 2.1 3.15 3.85	1.5 2.1 3.15 3.85	1.5 2.1 3.15 3.85	V
VIL	Maximum Low–Level Input Voltage, Enable Inputs		2.0 3.0 4.5 5.5	0.5 0.9 1.35 1.65	0.5 0.9 1.35 1.65	0.5 0.9 1.35 1.65	V
I _{IN}	Maximum Input Leakage Current, Enable Inputs	$V_{IN} = 5.5 V \text{ or GND}$	0 V to 5.5 V	<u>+</u> 0.1	<u>+</u> 1.0	<u>+</u> 1.0	μΑ
ICC	Maximum Quiescent Sup- ply Current (per package)	Enable and VIS = V_{CC} or GND	5.5	1.0	1.0	2.0	μΑ

DC ELECTRICAL CHARACTERISTICS – Analog Section

				Guaranteed Max Limit		.imit	
Symbol	Parameter	Condition	V _{CC}	–55 to 25°C	<85°C	<125°C	Unit
R _{ON}	Maximum On Resistance (Figures 8 – 12)	$V_{IN} = V_{IH}$ $V_{IS} = V_{CC} \text{ to GND}$ $I_{IS}I = \le 10.0 \text{mA}$	3.0 4.5 5.5	45 30 25	50 35 30	55 40 35	Ω
R _{FLAT(ON)}	On Resistance Flatness	$V_{IN} = V_{IH}$ $I_{IS}I = \le 10.0 \text{ mA}$ $V_{IS} = 1 \text{ V}, 2 \text{ V}, 3.5 \text{ V}$	4.5	4.0	4.0	5.0	Ω
I _{NO(OFF)}	Off Leakage Current, Pin 2 (Figure 3)		5.5	1.0	10	100	nA
I _{COM(OFF)}	Off Leakage Current, Pin 1 (Figure 3)	V _{IN} = V _{IL} V _{NO} = 4.5 V or 1.0 V V _{COM} = 1.0 V or 4.5 V	5.5	1.0	10	100	nA

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

					Guaranteed Max Limit								
			v_{cc}	-5	5 to 25	5°C		<85°C			<125°C	;	
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
t _{ON}	Turn-On Time	$R_L = 300 \Omega$, $C_L = 35 pF$ (Figures 4, 5, and 13)	2.0 3.0 4.5 5.5		7.0 5.0 4.5 4.5	14 10 9.0 9.0			16 12 11 11			16 12 11 11	ns
toff	Turn-Off Time	R_L = 300 Ω , C_L = 35 pF (Figures 4, 5, and 13)	2.0 3.0 4.5 5.5		11.0 7.0 5.0 5.0	22 14 10 10			24 16 12 12			24 16 12 12	ns

		Typical @ 25, VCC = 5.0 V	
C _{IN}	Maximum Input Capacitance, Select Input	8.0	pF
C _{NO or} C _{NC}	Analog I/O (switch off)	10	
C _{COM(OFF)}	Common I/O (switch off)	10	
C _{COM(ON)}	Feedthrough (switch on)	20	

			٧ _{cc}	Limit	
Symbol	Parameter	Condition	v	25°C	Unit
BW	Maximum On–Channel –3dB Bandwidth or Minimum Frequency Response	$V_{IS} = 0 \text{ dBm}$ V_{IS} centered between V_{CC} and GND (Figures 6 and 14)	3.0 4.5 5.5	190 200 220	MHz
V _{ONL}	Maximum Feedthrough On Loss	V_{IS} = 0 dBm @ 10 kHz V_{IS} centered between V_{CC} and GND (Figure 6)	3.0 4.5 5.5	-2 -2 -2	dB
V _{ISO}	Off-Channel Isolation	f = 100 kHz; V_{IS} = 1.0 V RMS V _{IS} centered between V _{CC} and GND (Figures 6 and 15)	3.0 4.5 5.5	-93	dB
Q	Charge Injection Enable Input to Common I/O		3.0 5.5	1.5 3.0	рС
THD	Total Harmonic Distortion THD + Noise	$\label{eq:FIS} \begin{array}{l} F_{IS} = 20 \text{ Hz to 1 MHz}, \ R_L = Rgen = 600 \ \Omega, \ C_L = 50 \ pF \\ V_{IS} = 3.0 \ V_{PP} \ sine \ wave \\ V_{IS} = 5.0 \ V_{PP} \ sine \ wave \end{array}$ (Figure 17)	3.3 5.5	0.3 0.15	%

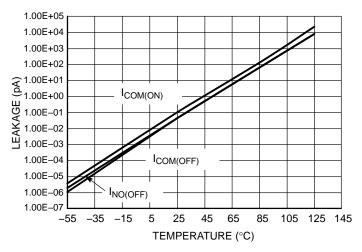
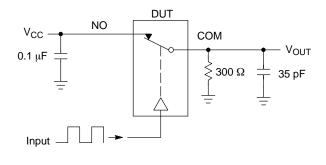
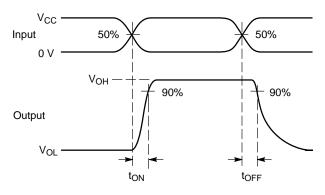
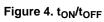


Figure 3. Switch Leakage vs. Temperature







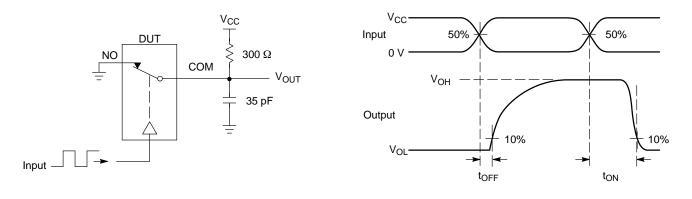
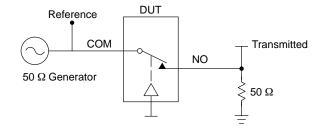


Figure 5. t_{ON}/t_{OFF}



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO} , Bandwidth and V_{ONL} are independent of the input signal direction.

$$\begin{split} & \mathsf{V}_{\mathsf{ISO}} = \mathsf{Off} \ \mathsf{Channel} \ \mathsf{Isolation} = 20 \ \mathsf{Log} \ \left(\frac{\mathsf{V}_\mathsf{OUT}}{\mathsf{V}_\mathsf{IN}}\right) \ \mathsf{for} \ \mathsf{V}_\mathsf{IN} \ \mathsf{at} \ 100 \ \mathsf{kHz} \\ & \mathsf{V}_\mathsf{ONL} = \mathsf{On} \ \mathsf{Channel} \ \mathsf{Loss} = 20 \ \mathsf{Log} \ \left(\frac{\mathsf{V}_\mathsf{OUT}}{\mathsf{V}_\mathsf{IN}}\right) \ \mathsf{for} \ \mathsf{V}_\mathsf{IN} \ \mathsf{at} \ 100 \ \mathsf{kHz} \ \mathsf{to} \ 50 \ \mathsf{MHz} \end{split}$$

Bandwidth (BW) = the frequency 3.0 dB below V_{ONL}

Figure 6. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}

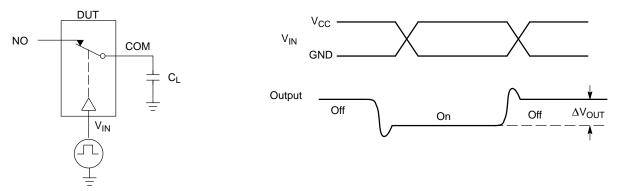
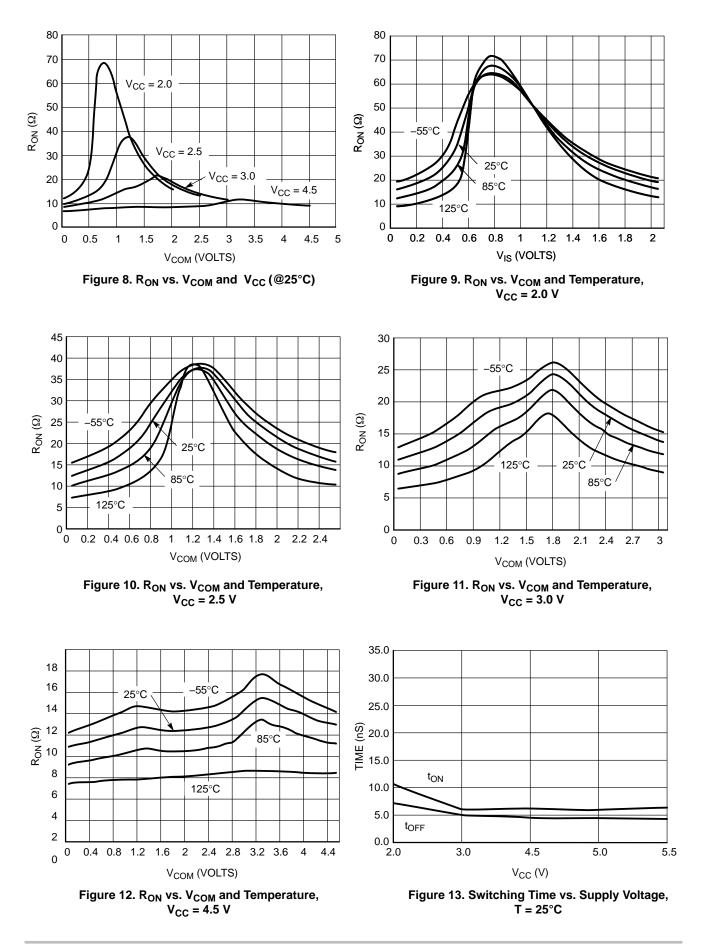
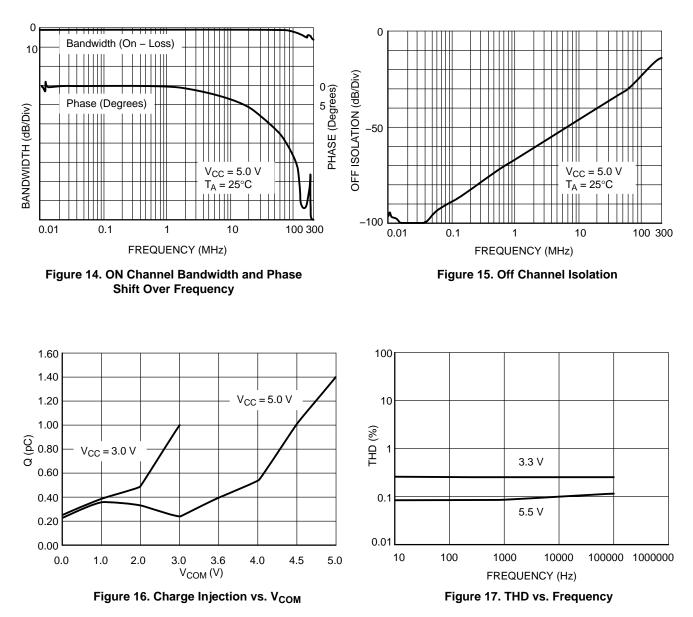


Figure 7. Charge Injection: (Q)



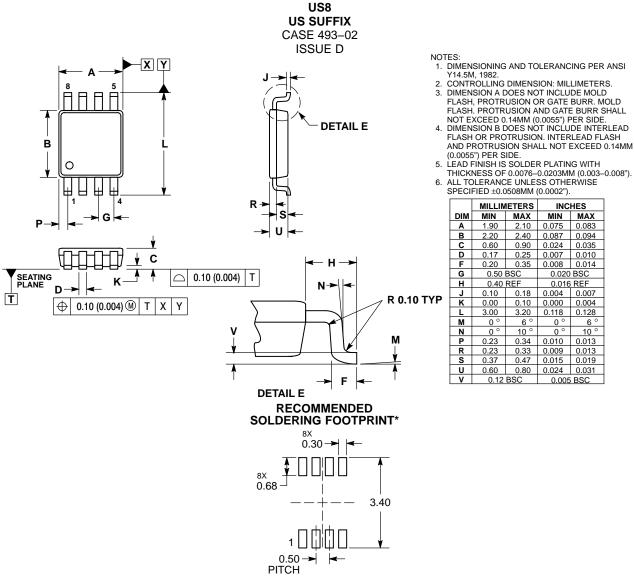


DEVICE ORDERING INFORMATION

Device Order Number	Package	Shipping [†]
NLAS323USG	US8 (Pb–Free)	3000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS



DIMENSIONS: MILLIMETERS

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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